

# Si4963DY

# **Dual P-Channel 2.5V Specified PowerTrench® MOSFET**

## **General Description**

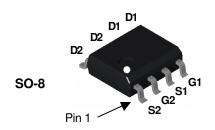
This P-Channel 2.5V specified MOSFET is a rugged gate version of Fairchild Semiconductor's advanced PowerTrench process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V - 12V).

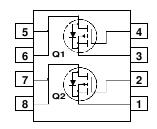
## **Applications**

- Load switch
- Motor drive
- DC/DC conversion
- Power management

### **Features**

- -6.2 A, -20 V,  $R_{DS(ON)} = 33$  m $\Omega$  @ V  $_{GS} = -4.5$  V  $R_{DS(ON)} = 50$  m $\Omega$  @ V  $_{GS} = -2.5$  V
- Extended V<sub>GSS</sub> range (±12V) for battery applications
- Low gate charge
- High performance trench technology for extremely low  $R_{DS(ON)}$
- High power and current handling capability





# **Absolute Maximum Ratings** T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
$V_{DSS}$	Drain-Source Voltage	-20	V	
$V_{GSS}$	Gate-Source Voltage		±12	V
l <sub>D</sub>	Drain Current - Continuous	(Note 1a)	-6.2	Α
	– Pulsed	Ī	-40	
P <sub>D</sub>	Power Dissipation for Dual Operation		2	W
	Power Dissipation for Single Operation	(Note 1a)	1.6	
		(Note 1b)	1	
		(Note 1c)	0.9	
$T_J$ , $T_{STG}$	Operating and Storage Junction Temperat	-55 to +175	°C	

### **Thermal Characteristics**

R <sub>0JA</sub>	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
R <sub>0</sub> JC	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

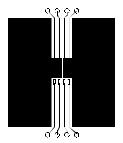
Package Marking and Ordering Information

_		<u> </u>	<u> </u>			
-	Device Marking Device		Reel Size	Tape width	Quantity	
-	4963	Si4963DY	13"	12mm	2500 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics			ı		
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-20			V
<u>ΔBV DSS</u> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu A$ , Referenced to 25°C		-16		mV/°C
l <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V},  V_{GS} = 0 \text{ V}$			-1	μΑ
Igssf	Gate-Body Leakage, Forward	$V_{GS} = -12 \text{ V},  V_{DS} = 0 \text{ V}$			-100	nA
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	$V_{GS} = 12 \text{ V},  V_{DS} = 0 \text{ V}$			100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{CS}, I_D = -250 \mu A$	-0.6	-1.0	-1.5	V
ΔVGS(th) ΔTJ	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu A$ , Referenced to 25°C		3		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	$V_{GS} = -4.5 \text{ V},  I_D = -6.2 \text{ A}$ $V_{GS} = -2.5 \text{ V},  I_D = -5 \text{ A}$ $V_{GS} = -4.5 \text{ V}, I_D = -6.2 \text{A},$ $T_J = 125^{\circ}\text{C}$		23 34 45	33 50 56	mΩ
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, \qquad V_{DS} = -5 \text{ V}$	-15			Α
<b>g</b> FS	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_D = -6.2 \text{ A}$		19		S
Dynamic	Characteristics					
Ciss	Input Capacitance	$V_{DS} = -10 \text{ V},  V_{GS} = 0 \text{ V},$		1456		pF
Coss	Output Capacitance	,,		300		pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1.0 MHz		150		pF
Switchir	g Characteristics (Note 2)					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = -10 \text{ V}, \qquad I_D = -1 \text{ A},$		15	27	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, \qquad R_{GEN} = 6 \Omega$		11	20	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			57	91	ns
t <sub>f</sub>	Turn-Off Fall Time			37	59	ns
Qg	Total Gate Charge	$V_{DS} = -10 \text{ V}, \qquad I_D = -6.2 \text{ A},$		14	20	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = -4.5 \text{ V}$		3		nC
$Q_{gd}$	Gate-Drain Charge			5		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
ls	Maximum Continuous Drain-Source	ÿ			-1.3	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V},  I_S = -1.3 \text{ A}  \text{(Note 2)}$		-0.7	-1.2	V

#### Notes

 R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>BJC</sub> is guaranteed by design while R<sub>BCA</sub> is determined by the user's board design.



a) 78°C/W when mounted on a 0.5ir<sup>2</sup> pad of 2 oz copper



125°C/W when mounted on a 0.02 in<sup>2</sup> pad of 2 oz copper



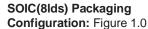
135°C/W when mounted on a minimum pad.

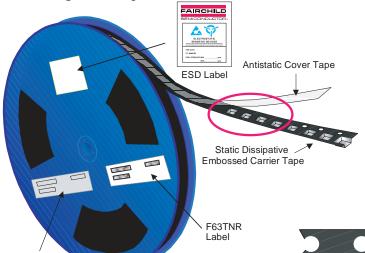
Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width <  $300\mu s,$  Duty Cycle < 2.0%

## **SOIC-8 Tape and Reel Data**







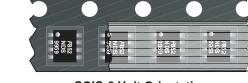
#### Packaging Description:

SOIC-8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13° or 330cm diameter reel. The relea are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 500 units per 7° or 177cm diameter reel. This and some other options are further described in the Packaging Information table.

These full reels are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.

**ESD Label** 

F63TN Label

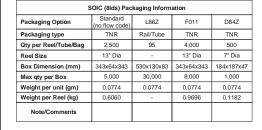


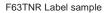
343mm x 342mm x 64mm Standard Intermediate box



F63TNI

**SOIC-8 Unit Orientation** 

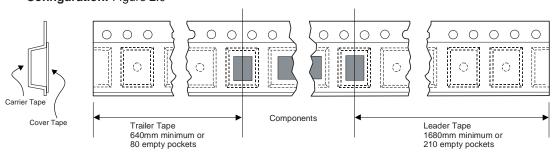




Customized Label

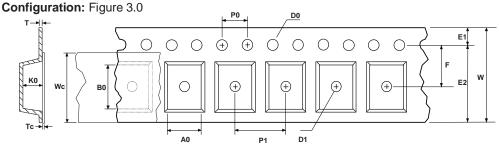


# SOIC(8lds) Tape Leader and Trailer Configuration: Figure 2.0





# SOIC(8lds) Embossed Carrier Tape



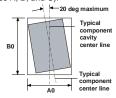


	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOIC(8lds) (12mm)	6.50 +/-0.10	5.30 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	2.1 +/-0.10	0.450 +/- 0.150	9.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



Sketch B (Top View)

Component Rotation



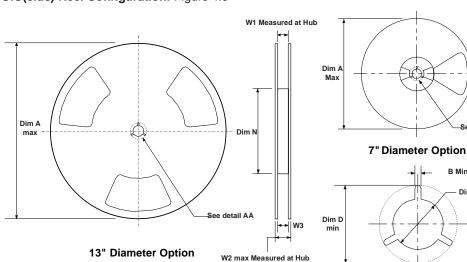
Sketch C (Top View)

Component lateral movement

Dim C

DETAIL AA

## SOIC(8lds) Reel Configuration: Figure 4.0

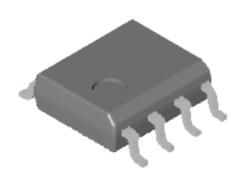


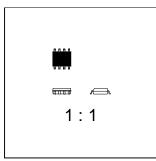
Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

# **SOIC-8 Package Dimensions**



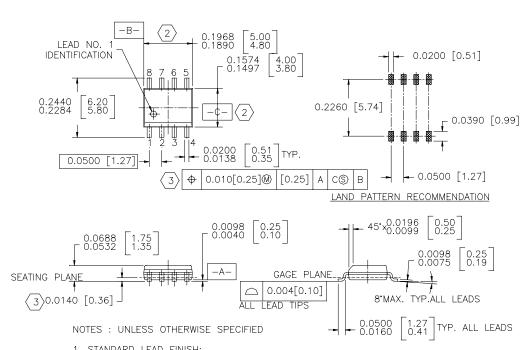
# SOIC-8 (FS PKG Code S1)





Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0774



1. STANDARD LEAD FINISH:
200 MICROINCHES / 5.08 MICRONS MINIMUM
LEAD / TIN (SOLDER) ON COPPER.

SO 0.150 WIDE 8 LEADS

- THESE DIMENSIONS DO NOT INCLUDE MOLD FLASH
- MAXIMUM LEAD 0.024 [0.609]

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DOME™ ISOPLANAR™ Quiet Series™
E²CMOS™ MICROWIRF™ SILENT SWITC

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